





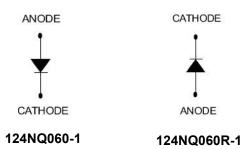
124NQ060/R-1 SCHOTTKY RECTIFIER



Features

- 125℃ T_J operation
- Unique high power, Half-Pak module
- Replaces three parallel DO-5'S
- Easier to mount and lower profile than DO-5'S
- High purity, high temperature epoxy encapsulation for enhanced
- · mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Baseplate: Nickel plated; Terminals: Nickel plated
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	60	V
Average Forward Current	I _{F(AV)}	50% duty cycle @T _C =76°C, rectangular wave form	120	А
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse	2880	Α
Non-Repetitive Avalanche Energy	E _{AS}	T _J =25°C,I _{AS} =20A,L=0.67mH	135	mJ
Repetitive Avalanche Current	lar	Current decaying linearly to zero in 1 μ sec Frequency limited by T_J max. V_A =1.5 \times V $_R$ typical	20	А

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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 120A, Pulse, T _J = 25 °C	0.49	0.54	V
	V F1	@ 240A, Pulse, T _J = 25 °C	-	0.71	V
	V_{F2}	@ 120A, Pulse, T _J = 125 °C	0.43	0.52	V
	V F2	@ 240A, Pulse, T _J = 125 °C	-	0.71	V
Reverse Current*	I _{R1}	@V _R = rated V _R , T _J = 25 °C	9	20	mA
	I _{R2}	@V _R = rated V _R , T _J = 125 °C	4000	6000	mA
Junction Capacitance	Ст	@V _R = 5V, T _C = 25 °C	4300	5200	pF
		f _{SIG} = 1MHz	4300	3200	PΓ
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

 $^{^{\}star}\,$ Pulse width < 300 $\mu s,\,$ duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification		Units
Junction Temperature	TJ	-	-55 to +125		°C
Storage Temperature	T _{stg}	-	-55 to	+125	°C
Typical Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	0.4	0	°C/W
Typical Thermal Resistance, case to Heat Sink	$R_{ heta cs}$	Mounting surface, smooth and greased	0.15		°C/W
Mounting Torque	Тм	Non-lubricated threads	Mounting Torque Terminal Torque	23(min) 29(max) 35(min) 46(max)	Kg-cm
Approximate Weight	wt	-	25.6		g
Case Style	PRM1-1				

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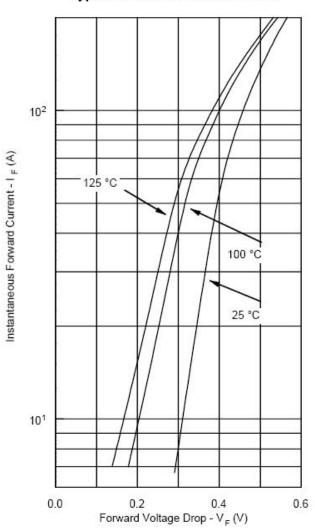




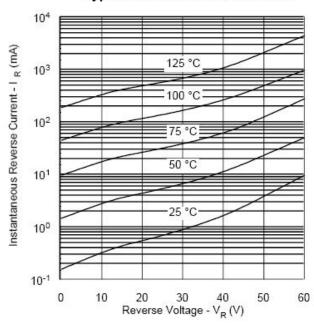


Ratings and Characteristics Curves

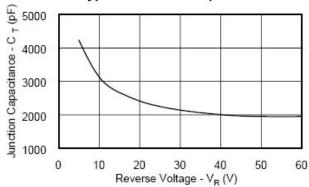
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



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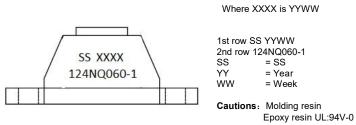


Ordering Information

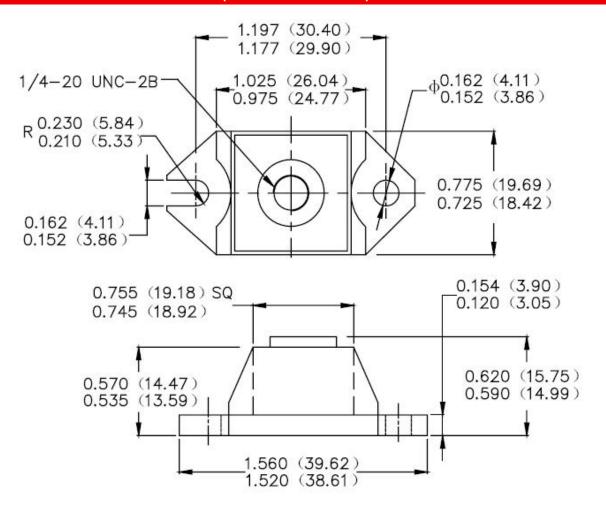
Device	Package	Shipping	
124NQ060(R)-1	PRM1-1(Pb-Free)	27pcs/ box	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Mechanical Dimensions PRM1-1 (Inches/Millimeters)



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